

The influence of the dimensions of CdSe/Cd_{1-x}Zn_xS core/shell type-I heterostructured quantum dots on the performances of light-emitting devices

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We have investigated the relationship between the dimensions of core/shell heterostructured quantum dots (QDs) with the performances of light-emitting diodes (LEDs). For comparative study, we have synthesized a series of CdSe/Zn_{1-x}Cd_xS core/shell type-I heterostructured QDs having similar optical properties (e.g., photoluminescence energy, full width at half maximum, photoluminescence quantum yield, single exciton lifetime) but varying shell thicknesses (core radius: 2.0 nm, 2.5 nm ≤ shell thickness ≤ 6.3 nm). Upon the inverted device architecture, thick-shell QDs have shown higher efficiency and operational stability along the current sweep within the actual devices. Spectroscopic analysis reveals that the suppression of energy transfer and QD charging in thick-shell QDs is indeed responsible for the improved device performances. As an ultimate achievement, deep-red QD-LEDs (λ_{max} = 630 nm) exhibiting peak external quantum efficiency of 7.4 % and record-high brightness above 100,000 cd/m² could be realized based on the type-I giant QDs (core radius: 2.0 nm, shell thickness: 6.3 nm).